Room temperature Mott hopping and high charge to spin conversion in amorphous Gd-alloyed BixSe1-x: A Candidate for Amorphous Topological Insulator

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Bismuth Selenide based thin films have generated a lot of interest because of their exotic transport properties. We investigated the transport property of Gd-alloyed BiₓSe₁₋ₓ (BSG) thin films. High resolution transmission electron microscopy (HRTEM) shows an amorphous film with occasional crystallites, close to the interface. The film is highly resistive, with respect to unalloyed-BiₓSe₁₋ₓ (BSG). Temperature dependent resistivity shows evident characters of variable range hopping transport, which persists close to room temperature. We have performed second harmonic transport characterization of BSG(t)/CoFeB( 5 nm) with different thickness of BSG (t= 6,8,12,16 nm), which allows us to separately analyze the spin-orbit torque and the thermally dependent magnetoresistance. The spin Hall angle deduced from the damping-like torque ranges from 1.27 to 3.74 at room temperature, depending on the thickness of BSG layer, which is one order of magnitude higher than that of heavy metals (HM). Our study indicates that the material is a strong candidate for amorphous topological insulator.
Bismuth selenide based materials have become extremely popular among condensed matter physicists because of their transport properties. Recent interests have garnered from the fact that these materials can exhibit topologically protected surface states [1-5]. These surface states are protected by time reversal symmetry, making them extremely important for various spintronic applications [6-9]. Many works have demonstrated efficient charge to spin conversion in topological insulator (TI) thin films [10-14]. However, film growth remains a major bottleneck for TIs, which usually requires molecular beam epitaxy (MBE) to grow highly ordered films on the appropriate substrate [15-17]. Recent work by our group indicate the presence of strong spin-orbit coupling (SOC) in sputtered polycrystalline Bi_xSe_1-x [18,19]. The existence of strong SOC in these polycrystalline films is surprising and interesting, which allows to explore novel physics in disordered TI materials. In most of TIs with highly ordered structure, the spin current generation is a result of spin-dependent momentum scattering in the surface states [20]. For highly disordered TI films, there are two major reasons to support the research motivation. First, studies have shown that bulk can sometimes play an important role for generation of spin current by traditional spin Hall effect, which also has become an important field of research [21]. Second, recent theoretical analyses have shown the existence of conducting surface states in amorphous films [22,23]. This can bring significant impacts to the field of topological spintronics. However, it requires state-of-the-art experiments to detect the presence of such surface states. Alloyed topological insulators can be a good candidate for the
disordered system, since these systems are amorphous and also demonstrate high charge-to-spin conversion. Effects of various impurities in TIs have also been extensively explored [19]. One important advantage is that by embedding magnetic moments inside alloys, one can create magnetic topological insulators for spin orbit torque (SOT) switching and Quantum Anomalous Hall effect [24,25]. Introduction of such impurities allows us to study the effects of disorder in such materials since they can have very different transport physics from the ordered ones. We also look at their effects on the resulting SOC of the film by growing a bilayer with a ferromagnet on the top. An important figure of merit used for these systems is spin Hall angle (SHA), which gives us the efficiency of the spin Hall channel to generate spin current from an injected charge current. The use of such spin Hall channels has been suggested for future MRAM structures that use SOT assisted switching of magnetic layer [26-29].

In this paper, we investigate the transport property of amorphous Gd-alloyed Bi\textsubscript{x}Se\textsubscript{1-x} (BSG) thin films grown by DC magnetron sputtering. Material characterization was performed by high resolution transmission electron microscopy (HRTEM) which shows a mainly amorphous feature of spin Hall channel. Strong temperature dependent conductivity was observed which indicates variable range hopping (VRH) transport mechanism [30]. Second harmonic transport measurements were performed on BSG (t=6,8,12,16 nm)/CoFeB(5 nm) samples with different BSG thickness[32,33]. High spin Hall angles are estimated at room temperature that range between 1.27-3.58 for varying thickness, which is one order of magnitude higher than that of heavy metals (HM)
Experimental

Bi-Se-Gd (40 %) (BSG) /Co40Fe40B20 (5 nm)/Ta films were grown by DC magnetron sputtering (with a base pressure 7 x 10^{-8} Torr) on thermally oxidized silicon substrate. Samples with different thickness of BSG (t = 6, 8, 12, 16 nm) were prepared. Unless otherwise stated, we label the samples as BSG6, BSG8, BSG12, BSG16 respectively. We also prepared a bare BSG (16 nm)/MgO (5 nm) sample for measuring resistivity at different temperatures.

High resolution transmission electron microscopy (HRTEM) and scanning transmission electron microscopy (STEM) were performed to characterize the interfacial structure using a probe corrected JEOL ARM 200 CF operated at 200kV. Thin lamella was extracted by focused ion beam (FIB) milling using an FEI Helios Nanolab dual beam. Electron energy loss spectroscopy (EELS) spectrum images (SI) were recorded in STEM mode with a Gatan Quantum Imaging filter ER. In order to correct energy drift and estimate the local thickness, the zero-loss and the core-loss spectra were simultaneously recorded for a dispersion of 1eV (Dual EELS method). The core loss spectra were registered in the range 670-2700 eV in order to record Fe_L, Co_L, Gd_M, Mg_K, Se_L Ta_M and Bi_M edges. B_K and O_K signals with edges respectively near 188 eV and 532eV, were not recorded. The pixel size of the SI was fixed at 0.4 nm for a dwell time of 0.5 s/pixel for the core loss spectra. After energy drift correction, the SI were denoised using a principal component analysis method [P. Potapov, P. Longo, and E. Okunishi., "Enhancement of noisy EDX HRSTEM spectrum-images by combination of filtering and PCA." Micron, 2017, 96, 29-37] before quantitative analysis. These films were then
patterned into Hall bars by standard photolithography process followed by Ar ion milling. Second step of photolithography involved exposing the contact areas. This was followed by metal contact deposition of Ti (10 nm) and Au (120 nm) by using e-beam evaporation.

Transport measurements were carried out on Quantum design PPMS 3000 which provides good temperature control, external field and a rotating stage. First harmonic measurements (temperature dependent resistance, Anomalous Hall effect) were done with Keithley 6221 as current source and nanovoltmeter to probe the DC voltage. Second harmonic transport measurements were carried out with an AC source to generate a sinusoidal input current of 1 mA RMS at 10 Hz frequency. A Stanford research SR830 was paired with an EG&G 7260 lock-in amplifier to read the first harmonic and second harmonic voltages respectively. Temperature dependent resistivity measurements were done to analyze the dominant transport mechanism. In order to analyze the spin orbit torque, second harmonic Hall voltages were recorded while rotating the sample with a constant magnetic field. This process was repeated for various magnetic field ranging from 0.06T to 3T. The second harmonic Hall voltage show a good cosine function with respect to the rotation angle. Amplitude was extracted from the fits of the angle dependent cosine function. These amplitudes were plotted as a function of the external field which allowed us to obtain the out-of-plane field corresponding to the damping-like torque. Anomalous Hall effect measurements were done by sweeping the magnetic field in out of plane direction from -3 T to +3 T. The field-like torque component and Oersted field were found negligible. Spin hall angles
were obtained from the damping-like torque with the corresponding error bars for various thickness of BSG.

**Results and Discussion**

Figure 1(a) shows an HRTEM image. From the bottom to the top one can see the amorphous silicon oxide substrate, followed by the working layers. A part of bottom MgO appears amorphous whereas the other part contains nanocrystalline and was identified as cubic MgO phase, with mainly (100) direction perpendicular to the layer. In some parts of this layer, darker contrasts are visible, due to the diffusion of heavy element in the MgO. The second layer composed of heavy elements (Bi, Se Gd) appears mainly amorphous but close to the surface of this layer, flat crystallites are dispersed in the amorphous matrix. The dark grey layer that corresponds to the CoFeB layer appears fully amorphous. On its top the second MgO layer appears well crystalline but without any preferential orientation. The top Ta capping layer appears partially oxidised at it’s surface on more than half of it thickness. This explains why this capping layer appears larger than that expected, due to the lower density of Ta oxide (Fig. 1(b)).

Figures 1(b) shows the HAADF image where EELS Spectrum image was recorded inside the white rectangular frame. After processing the spectrum images, quantitative element maps were drawn as shown figure 1(c). The chemical maps confirms the presence of silicon oxide in some part of the bottom MgO layer that can explain why a part of this layer appears amorphous (Fig 1(a)). As it can be seen on the Bi, Gd and Se maps, the composition of BSG layer is not homogeneous. The heavy element detected from BF images in the crystalline part of this layer is clearly Gd, and an over
concentration of Gd can be seen at the interface between the bottom MgO layer and the BSG layer. On the contrary, Se segregates at the surface of this layer. Gd, Bi and Se over concentration spots are clearly visible. The mean atomic concentration of this area was evaluated as Bi 20%, Se 40%, Gd 40%. The ratio between Co and Fe in the ferromagnetic CFB layer was evaluated to be ¼. A tiny diffusion of Fe and Co through the top MgO layer was detected.

Fig. 2 shows the temperature dependent resistivity of BSG (16 nm) films. The resistivity shows a very strong temperature dependence and changes by a factor of 20 as cooling from 300 K to 80 K. We compare the temperature dependent conductivity for Arrhenius type dependence, which is the most popular mechanisms. This kind of temperature dependence corresponds to variable range hopping (VRH) conduction, which can be divided into three categories: 1) Efros-Shklovskii (ES) VRH, 2) 2D Mott VRH and 3) 3D Mott VRH. VRH mechanism is usually dominant in disordered films with strong localization near the Fermi level. This results in electrons hopping from one site to another, which is usually a combination of tunneling and thermal jumps, originating from phonon vibrations [34]. In VRH, the hopping length and hopping energy can vary from one site to another. The average value of the hopping energy, depends on the average hopping length and density of states at Fermi level. However, later Efros and Shklovskii pointed out that, at low enough temperatures, the density of states near fermi level changes linearly for a 2D system owing to the coulomb interaction between the electron and the hole. This results in a very distinct temperature dependent conductivity.
The relation between conductivity and temperature for VRH is given as follows:

\[ \sigma = \sigma_0 \exp \left[-\left(\frac{T_0}{T}\right)^p\right] \]  

(1)

Here \( \sigma_0 \) is the conductivity parameter and \( T_0 \) is the characteristic Mott/ES temperature. The exponents, \( p=0.5, 0.33, 0.25 \) for ESVRH, 2D VRH, 3D VRH respectively. Fig. 2(c) shows \( \log(\sigma) \) vs \( (1/T)^{0.25} \) which shows a strong linear behavior, with negative slope, between 100K-300K. Fig 2(a,b,c) show the ESVRH, 2D Mott and 3D Mott VRH fit, respectively. Rigorous data analyses show a best fit with 3D Mott hopping, based on the residual sum of squares (RSS) for each of the fit. This is a strong indication that, 3D Mott hopping is a dominant transport mechanism in our film.

The conductance described by 3D Mott hopping can be expressed by the following equation:

\[ \sigma_0 = 3e^2 \vartheta_{ph} \left(\frac{N(E_F)}{8\pi\alpha k_B}\right)^{1/2} \]  

(2)

Where \( N(E_F) \) is the density of states at the Fermi level, \( \alpha \) is the inverse localization length and \( \vartheta_{ph} \) is the frequency of optical phonons (~10^{13} Hz) [Ref?]. The degree of disorder in the film with a characteristic temperature \( T_0 \) can be obtained from the fit of temperature dependent conductance:

\[ T_0 = \frac{\lambda \alpha^3}{k_B N(E_F)} \]  

(3)

Here \( \lambda \) is a dimensionless constant with a value of 18.1 [Ref?]. The relation for the conductivity parameter is based on an assumption that, the dominant scattering
mechanism in the sample is electron-phonon interaction. This relation can change depending on the prevalent scattering mechanism, which can also be a combination of various scattering mechanisms. The value of $T_0$ obtained from the fit is $2.2 \times 10^6$ K, which is quite high, indicating very strongly that the amount of disorder in the film must be high [34-36]. Using this value with the electron-phonon interaction relation for $\sigma_0$ gives unphysical results for the inverse localization length and density of states. Hence, this points to the fact that electron-phonon interaction may not be the dominant scattering mechanism for this sample.

We further characterized the SOT of BSG by adding an extra ferromagnetic layer (CFB 5nm), with in-plane anisotropy on top. The current flowing through the spin Hall channel will produce two different kinds of torques: Field-like ($\vec{m} \times \vec{d}$) and damping-like ($\vec{m} \times (\vec{d} \times \vec{m})$) torque. Both these torques depend on the relative orientation between the spins and the magnetizations. The relative strength of these torques depend on the specific material. The respective effective fields, giving rise to the Hall voltage can be calculated by the second harmonic Hall response model [33]:

$$V_{2\omega} = \left( \frac{-H_{FL} + H_{Dl}}{H_{ext} - H_A} \right) R_p \cos(2\varphi) + \frac{1}{2} \frac{H_{DL}}{H_{K} - H_{ext}} R_A + V_t \cos(\varphi) + H_{ext} V_{NE} \cos(\varphi) \right) I \tag{4}$$

Here $H_A$ and $H_K$ are out of plane and in plane anisotropy, respectively. $H_{FL}$ and $H_{DL}$ are the effective fields due to field-like and damping-like torque. $R_p$ and $R_A$ are the planar Hall and anomalous Hall coefficients of the bilayer. $V_t$ is the thermal voltage created by the perpendicular temperature gradient created across the ferromagnetic layer. $V_{NE}$ is the Nernst effect, possibly generated from Bismuth in the spin Hall channel. $\varphi$ is the angle between the current and the in-plane field. By
angular dependence measurements, between the in-plane field and current channel at different external fields, we can separate the different contributions from the field-like, damping-like and thermal voltages. Fig. 3(a) shows the schematic of second harmonic measurement setup.

Thermal voltages can originate from any source that is sensitive to a temperature gradient across the ferromagnetic layer. This typically includes anomalous Nernst effect of the CoFeB layer. Hence, at high enough magnetic field, with respect to the saturation field of the ferromagnet, the Hall voltage should be almost entirely from thermal effects. Since the Nernst effect is proportional to the external magnetic field, the voltage related to the Nernst effect at smaller $H_{\text{ext}}$ can be separated. In our sample, this Nernst effect voltage was about 4-5 times smaller than the amplitude pertaining to the anti-damping torque. Fig 3(b) shows the anomalous Hall effect measured in bilayer ($t = 8$ nm), which indicates that the magnetization of 5nm CFB film has a saturation point around 1.5 T.

Fig. 4(a) shows the second order Hall signal at 3T external field. As it can be seen, the data shows a good cosine characteristic that can be fitted to obtain the amplitude. Here, it turns out that at high enough external fields (0.06-3 T) the field-like torque and Oersted field is negligible since we don’t observe any $\cos(2\varphi)$ component in the second order Hall voltage. The field-like torque is often observed as small depression in the second harmonic Hall voltage around 90 and 270 degrees [33]. The fitted amplitudes are then plotted against $\frac{1}{H_{K}-H_{\text{ext}}}$ in Fig. 4(b), which is further processed by a linear fitting. The slope of the linear fit allows us to determine
the damping-like field and the intercept gives out the thermal voltage. The deviation of the amplitudes from the linear fit is used to obtain the errors in damping-like field. The damping-like field is related to the spin current generated form the spin Hall channel: $H_{DL} = \frac{\hbar J_S}{2eM_{StFM}}$ [19]. Here $J_S$ is the spin current generated from the BSG layer. Using this relationship, we can calculate the spin Hall angle which is defined as the ratio of the spin current generated from spin Hall channel over the charge current injected with the following equation [ref?].

$$\theta_{SH} = \frac{J_S}{J_C} = \frac{2eM_{StFM}H_{DL}}{\hbar J_{SHM}} \tag{5}$$

Here $M_S$ is the saturation magnetization of the magnetic film and $J_{SHM}$ is the current density through the spin Hall channel, which is calculated by the current shunting method. We have performed the angular dependent second order Hall measurement on the BSG/CFB bilayers with different thickness of BSG, and deduced spin Hall angles from the obtained damping-like torque $H_{DL}$ and injecting into the Eq. [5]. The spin Hall angles are in the range of 1.27-3.58, as shown in Fig.5. This is almost one order of magnitude higher than most heavy metals. Mathematically, the large spin Hall angle is owed to the fact that the amount of charge current through the BSG layer is small because of the small current density. However, the actual reason for the high charge to spin conversion depends on the spin-orbit coupling, Rashba-Edelstein effect and various other physics in the material level. The results obtained from pure BiSe samples are even higher [19].

One of the best ways to understand the physics of the high charge to spin conversion is to analyze the thickness dependence. The thickness dependence of the
spin Hall angle peaks for BSG8 sample and then goes down with thicker samples. This is in contrast to the predicted and observed SOT dependence on thickness of spin Hall channel [37,38]. In the theoretical works, the spin current at the interface is calculated from the drift-diffusion model that gives rise to the spin accumulation at the interface, by applying appropriate boundary conditions[Ref?]. In this model the spin current, originating from the bulk, is not taken into consideration. Taking the bulk spin generation into account can considerably change the thickness dependence of spin Hall angles [39]. The spin Hall angle can peak for a certain thickness of spin Hall channel depending on the spin diffusion length in the material. If the sample is too thin, this will give rise to a small spin current since the amount of material to generate the spin current is small. On the other hand, a too thick spin Hall channel will generate strong spin current but the spin currents can be diffused before reaching the interface. This gives rise to a optimized thickness where the SHA is maximum, as seen in Fig. 5. This is in strong contrast with unalloyed Bismuth Selenide, where the spin Hall angle consistent increases as the thickness of spin Hall channels decreases [18]. It is an indication that most of the spin current is generated from the bulk of the BSG. In most ideal topological insulators the spin current generated can be from two major sources. Firstly, it can be from the surface states of TIs [40,41]. Typically the symmetry protected surface states can give rise to strong Rashba-Edelstein effect which can generate interfacial spin polarization. The other source would be the bulk spin Hall effect [21]. This is generated from the traditional spin Hall effect as in the most of systems with heavy metals. Spin polarized electron
generated from Rashba-Edelstein effect will depend strongly on the amount of current transported through the surface channels. However, the bulk conductivity is parasitic, creating additional current shunting, which is detrimental to the interfacial spin accumulation. Hence, decreasing the thickness can suppress these parasitic bulk effects, thereby increasing the current through the surface channels which leads to higher spin polarization. Hence, in unalloyed BiSe, the thickness dependence allows us to conclude a strong contribution from the surface conducting channels. Alloyn BiSe with Gd induces magnetic moments which could destroy the time reversal symmetry in the surface states [23-25]. Hence, in such cases, the surface is no longer a primary contributor to interfacial spin accumulation. The bulk/impurity spin Hall effect can become a majority contributor leading to the distinct thickness dependence which is observed in our case. Another possible explanation for this behavior could be the existence of topologically protected conducting surface states in our films as recent theoretical predictions [22,23], which can explain the high charge-to-spin conversion in BSG films. To verify this, we will build experiments with in-situ four probe scanning tunneling microscopy (STM) measurements to check the surface conductance in the future.

In conclusion, we have performed a detailed structural and spin transport characterization of Gd alloyed BiSe thin films. The TEM characterization reveals the BSG film is mostly amorphous. Temperature dependent resistivity measurements indicate a dominant hopping transport mechanism in the film. This hopping transport is a consequence of extra disorder in the Gd alloyed films as opposed to pure BiSe
films. We further performed second harmonic Hall characterization to quantify the spin Hall torque. The measurements showed a strong anti-damping torque component and a thermal component. The anti-damping component gave us the spin Hall angle, which is about one magnitude higher than most reported heavy metals. Our results show that the amorphous topological insulators could also generate a large charge-spin conversion, which could be interest for future spintronics applications.

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REFERENCES

FIGURE LEGENDS
FIG. 1. (a) High resolution transmission electron microscope image (b) STEM HAADF image at mid magnification with the white rectangle showing the region where the EELS Si was recorded (c) Elemental maps of the stacks drawn from EELS Si after quantitative processing with all the essential elements from the substrate to the capping layer. The tiny silicon signal visible in the Ta capping layer is due to an artefact of processing, due to the overlapping of TaM4 and of SiK edges repectively at 1793 and 1839 eV.

FIG. 2. Temperature vs log(conductivity) with various fits with known theoretical models. a-d shows the fits with ESVRH, 2D VRH, 3D VRH, Arrhenius respectively

FIG. 3. (a) Device transport measurement setup (b) corresponding anomalous Hall resistance for BSG8 at room temperature

FIG. 4. (a) Second harmonic Hall resistance as a function of angle for BSG8 at room temperature and 3T external field (b) Amplitude of second harmonic signal as a function of \( \frac{1}{H_{ext}-H_k} \)

FIG. 5. Spin Hall angle as a function of thickness of BSG layer.
Fig. 2
Fig. 3

(a) Diagram showing a setup with vectors and labels.

(b) Graph showing the relationship between magnetic field and a parameter, possibly $R_{xy}$.

Equation: $I = I_0 \sin(\omega t)$
Fig. 4
Fig. 5